

GM195A

PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

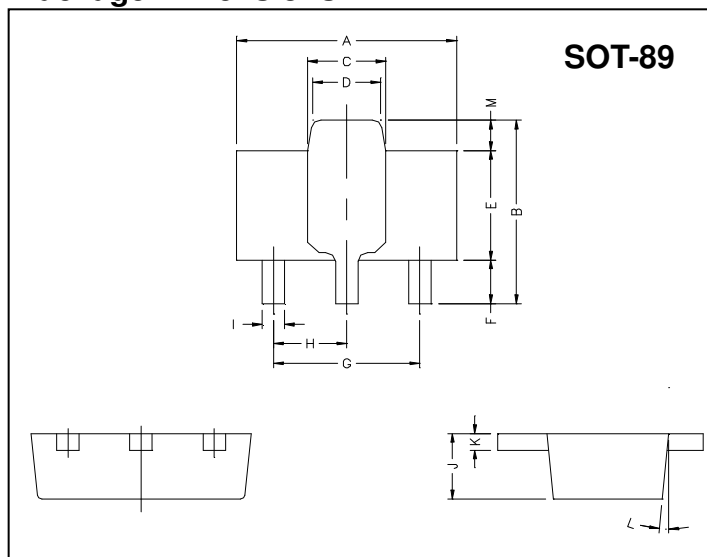
Description

The GM195A is designed for medium power amplifier applications.

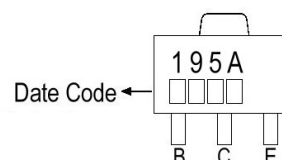
Features

- 1 Amp continuous current
- Complementary to GM194A

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	V _{CB0}	-40	V
Collector to Emitter Voltage	V _{CE0}	-40	V
Emitter to Base Voltage	V _{EB0}	-5	V
Collector Current (DC)	I _C	-1	A
Collector Current (Pulse)	I _c	-2	A
Total Power Dissipation	P _D	1	W

Electrical Characteristics (Ta = 25°C, unless otherwise stated)

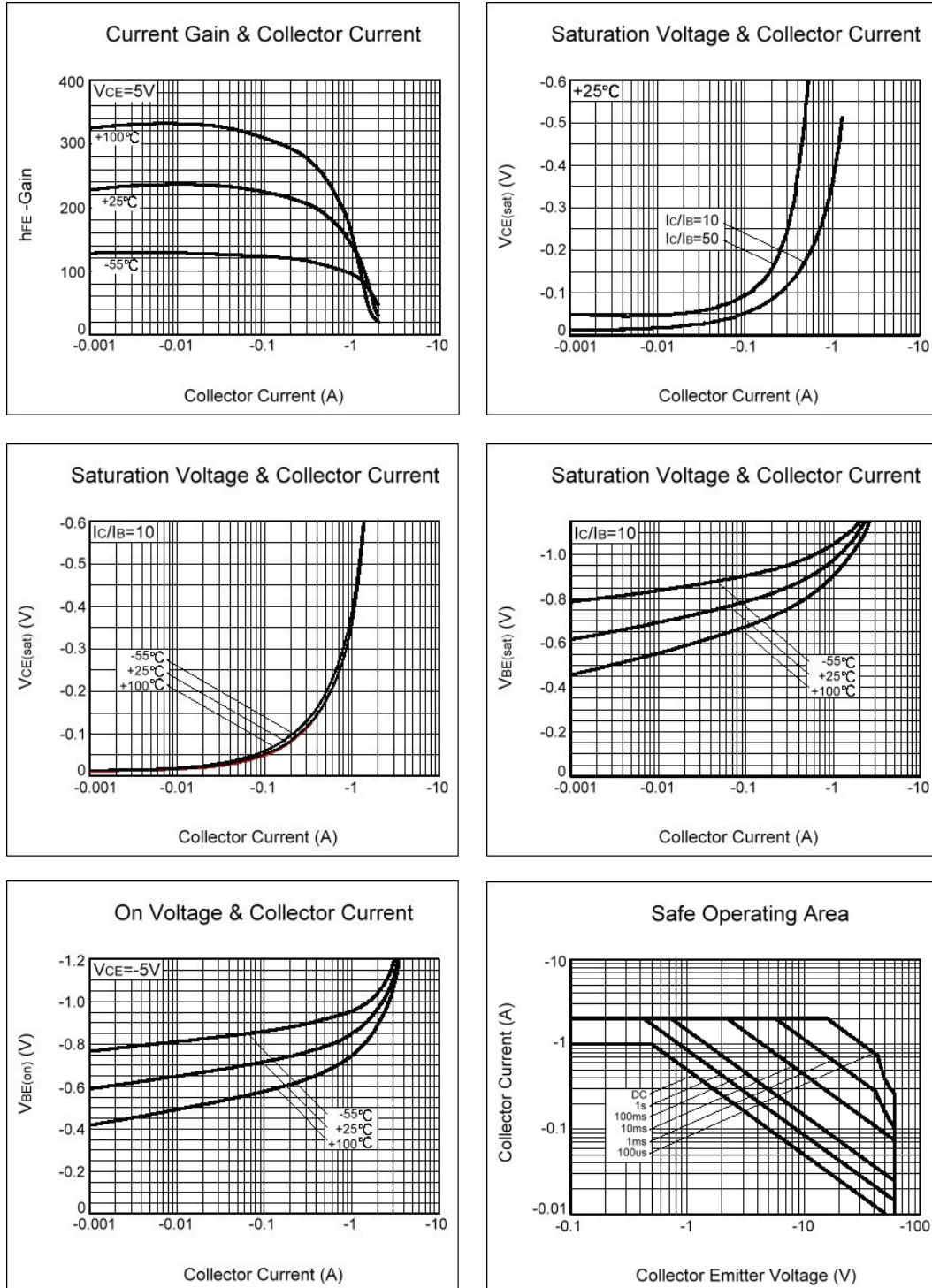
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V _{CB0}	-40	-	-	V	I _C =-100uA, I _E =0
*V _{CE0}	-40	-	-	V	I _C =-10mA, I _B =0
V _{EB0}	-5	-	-	V	I _E =-100uA, I _C =0
I _{CB0}	-	-	-100	nA	V _{CB} =-30V, I _E =0
I _{CES}	-	-	-100	nA	V _{CE} =-30V
I _{EB0}	-	-	-100	nA	V _{EB} =-4V, I _C =0
*V _{CE(sat)} 1	-	-	-0.2	V	I _C =-100mA, I _B =-1mA
*V _{CE(sat)} 2	-	-	-0.35	V	I _C =-500mA, I _B =-20mA
*V _{CE(sat)} 3	-	-	-0.5	V	I _C =-1A, I _B =-100mA
*V _{BE(sat)}	-	-	-1.1	V	I _C =-1A, I _B =-50mA
*V _{BE(on)}	-	-	-1.0	V	V _{CE} =-5V, I _C =-1A
*h _{FE1}	300	-	-		V _{CE} =-5V, I _C =-1mA
*h _{FE2}	300	-	900		V _{CE} =-5V, I _C =-100mA
*h _{FE3}	250	-	-		V _{CE} =-5V, I _C =-500mA
*h _{FE4}	160	-	-		V _{CE} =-5V, I _C =-1A
*h _{FE5}	30	-	-		V _{CE} =-5V, I _C =-2A
f _T	150	-	-	MHz	V _{CE} =-10V, I _C =-50mA, f=100MHz
C _{ob}	-	-	10	pF	V _{CB} =-10V, I _E =0, f=1MHz

*Measured under pulse condition. Pulse width=300μs, Duty Cycle≤2%

Classification Of hFE2

Rank	P	Q
Range	300 ~ 700	500 ~ 900

Characteristics Curve



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